Supporting Information

Highly reversible sodium storage in GeP_5/C composite anode with large capacity and low voltage

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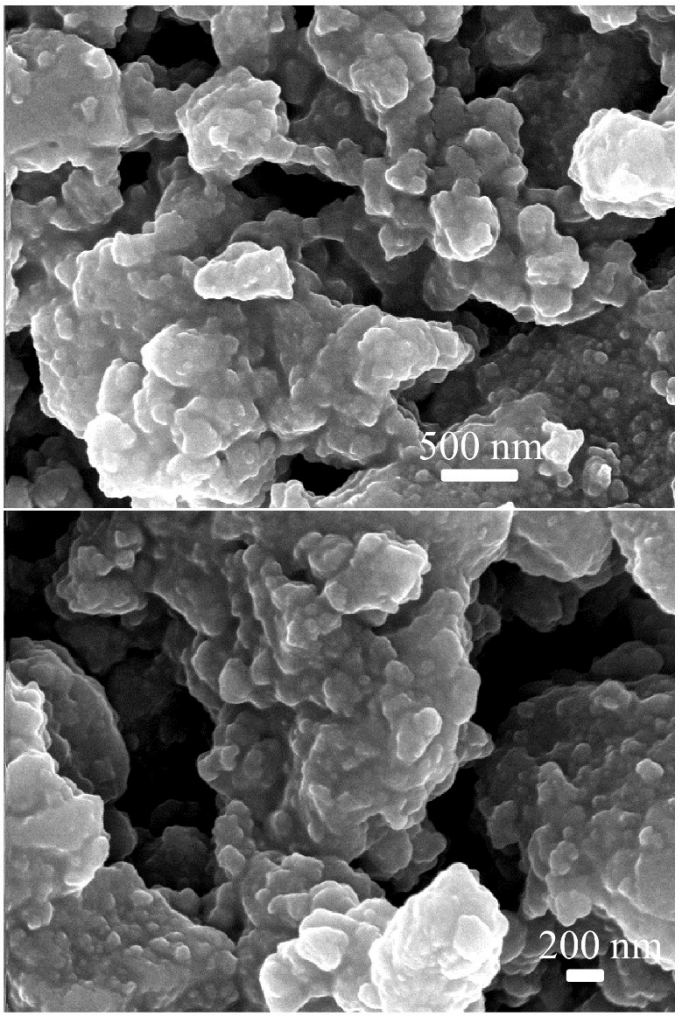

Figure S1. The high-magnification FSEM images taken on the agglomerated micro sized GeP_5 secondary grain.

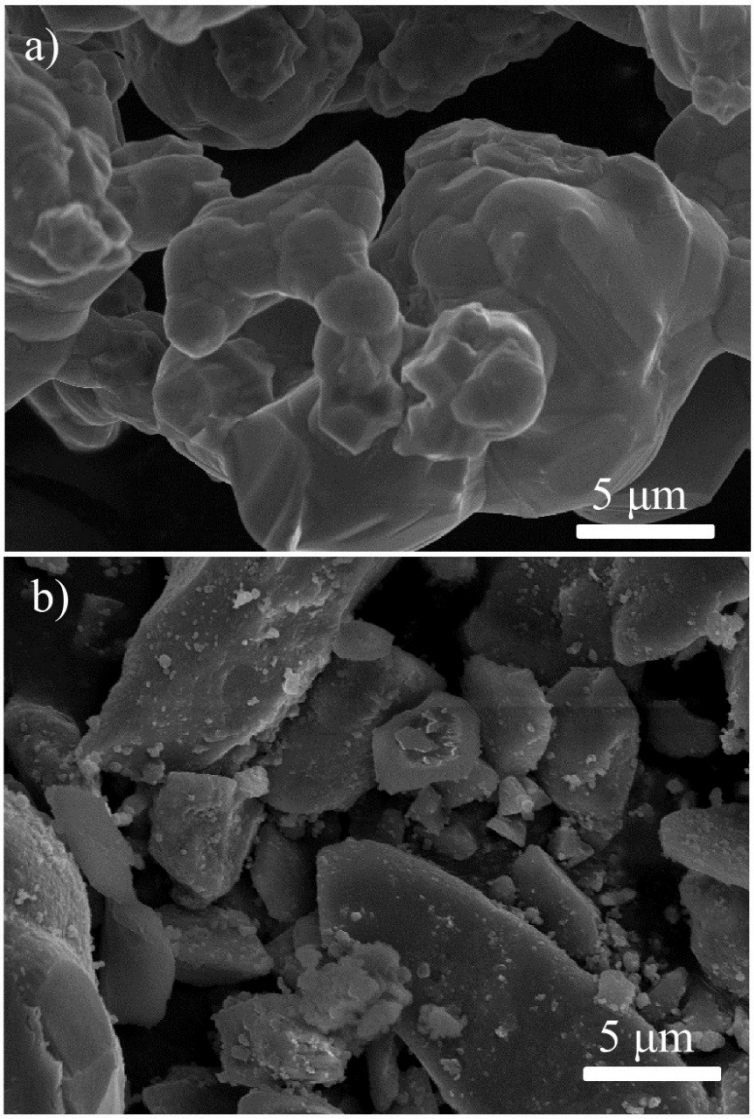

Figure S2. The FSEM images of (a) fresh Ge, and (b) P.

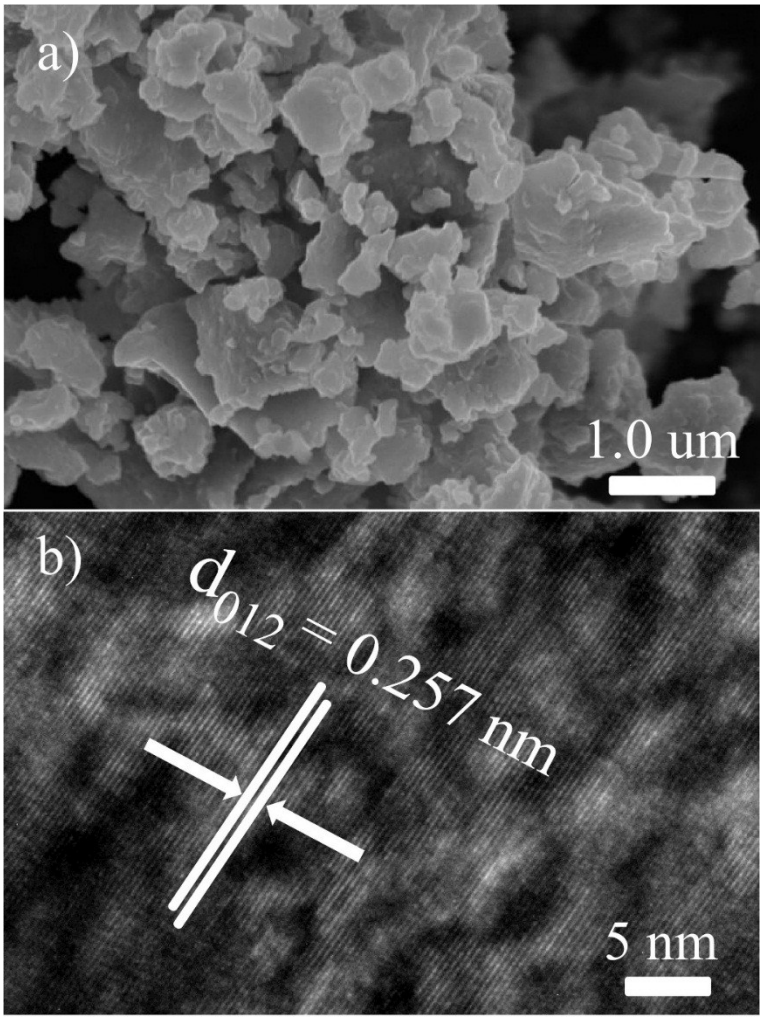

Figure S3. (a) The FSEM and HRTEM images of pure-phase GeP_5.

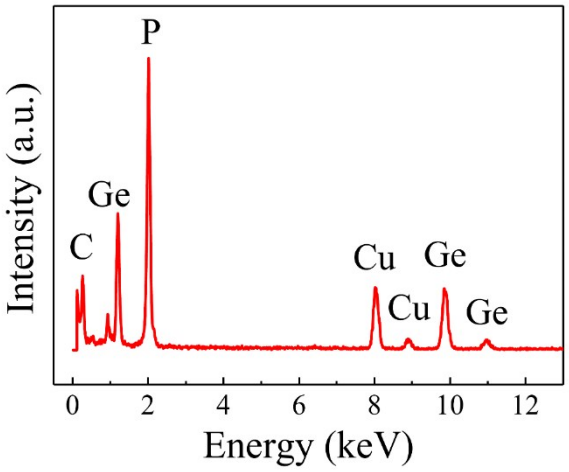

Figure S4. The EDX spectra of GeP_5/C composite.

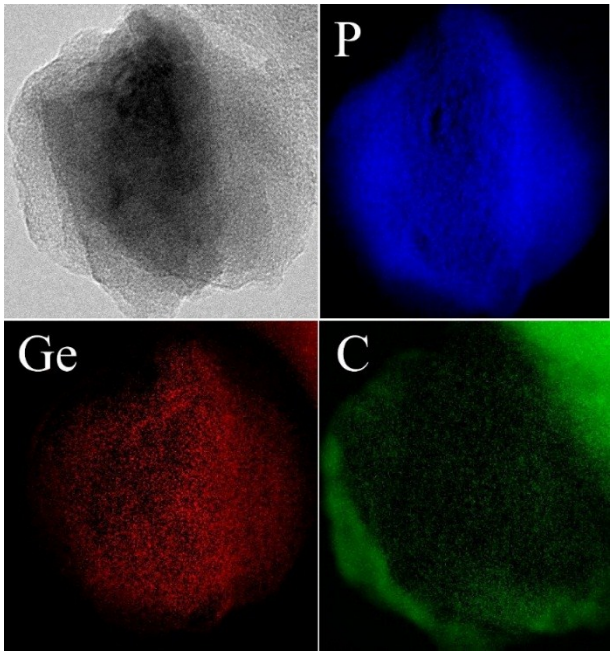

Figure S5. The individual elements distribution of of GeP_5/C (elemental mapping).

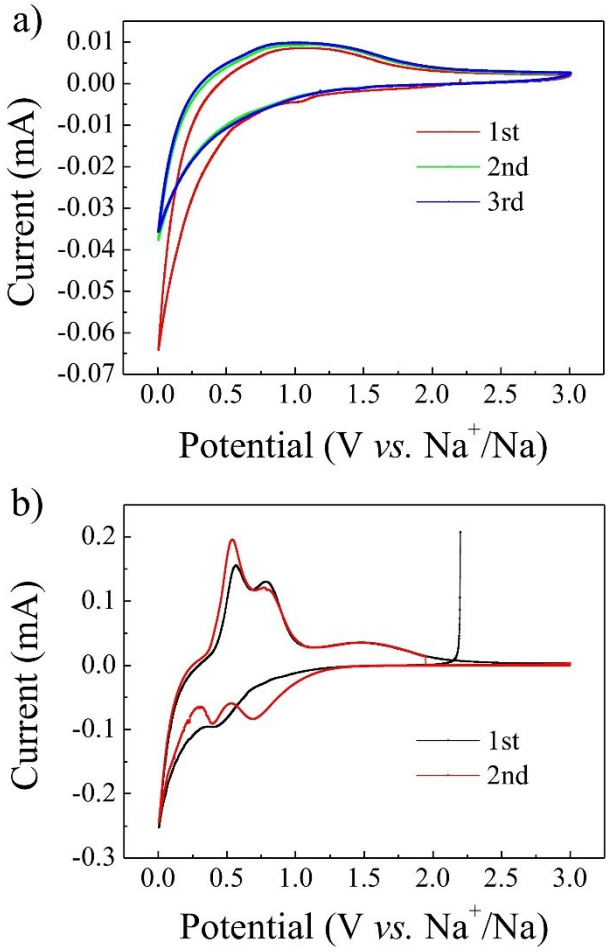

Figure S6. a) The initial three CV curves of Ge/C and b) P/C composite anode, respectively, at a scan rate of 0.05 mV s^{-1}.

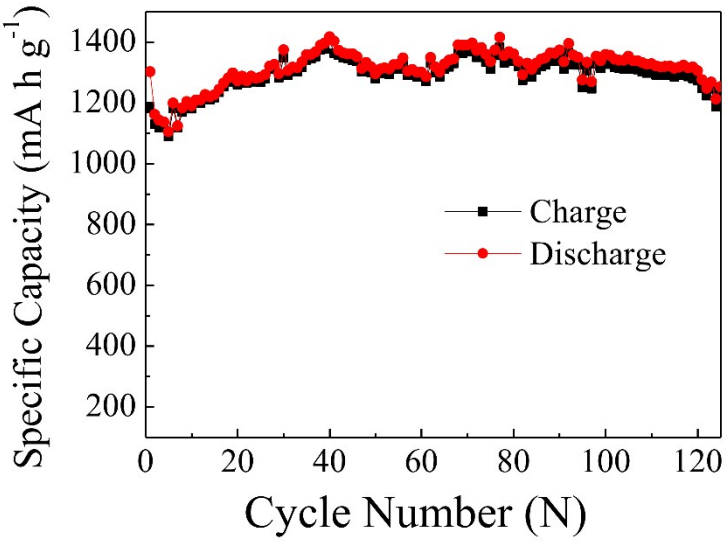

Figure S7. The cycle stability of GeP_5/C composite at a current density of 50 mA g^{-1}.

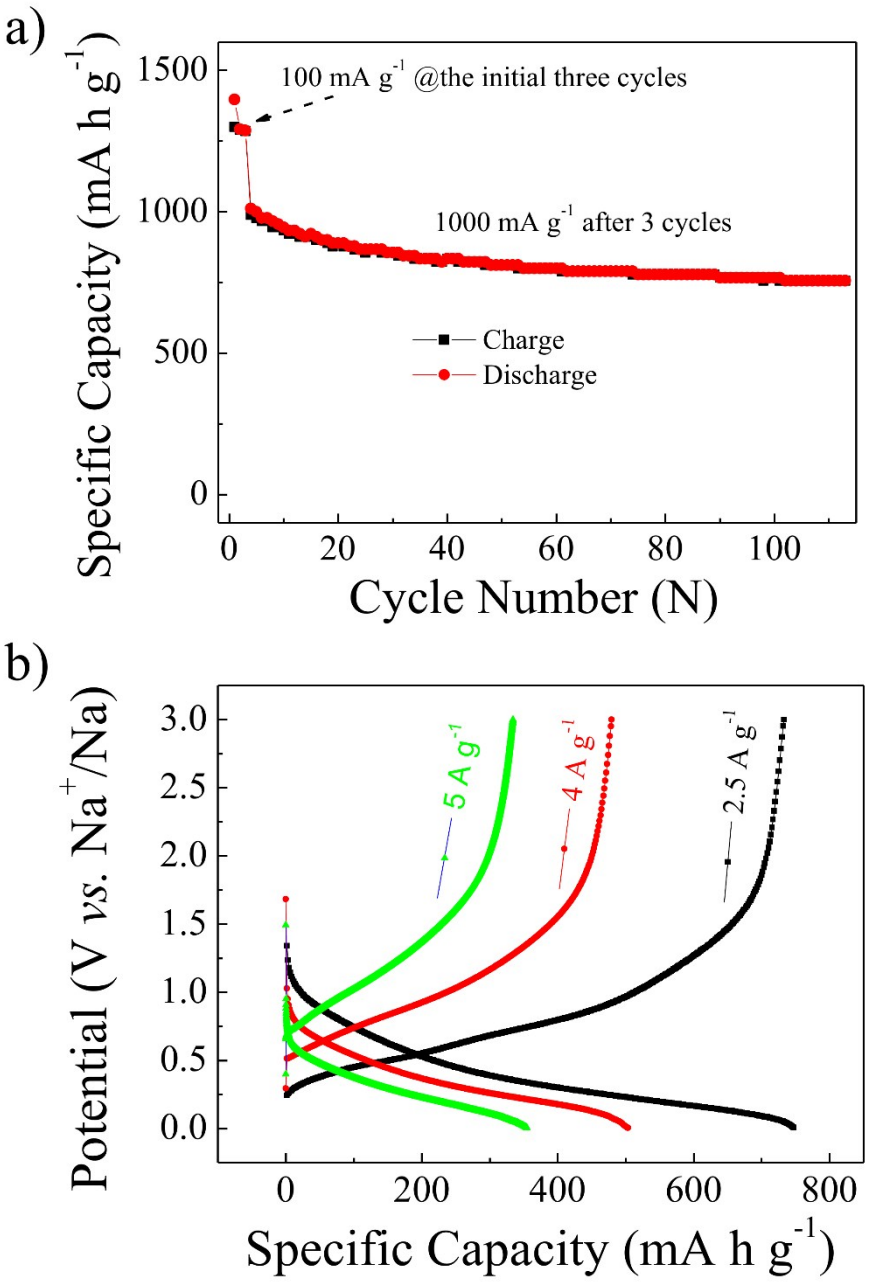

Figure S8. a) The cycle stability at the current density of 1000 mA g^{-1}; b) The higher rate performances of GeP_5/C composite.

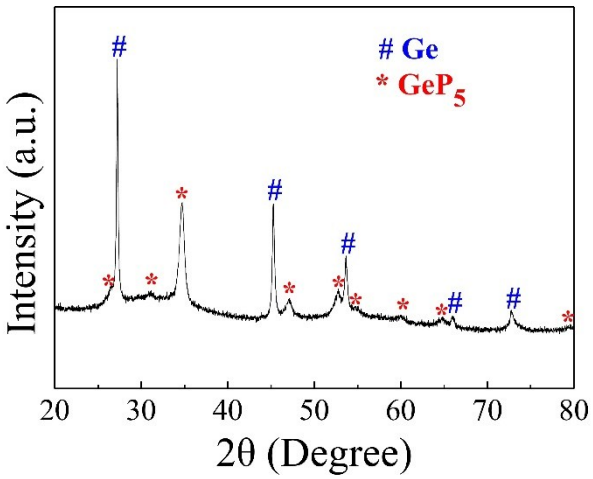

Figure S9. The XRD pattern of the mixture of GeP_5, P and Ge (marked as GeP_5-P-Ge).

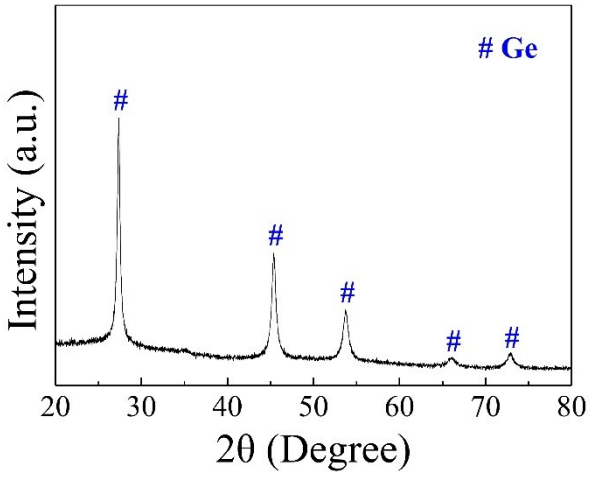

Figure S10. The XRD pattern of the mixture of Ge/C, and P/C (marked as Ge/C-P/C composite, and its atomic ratio of Ge:P is 1:5).

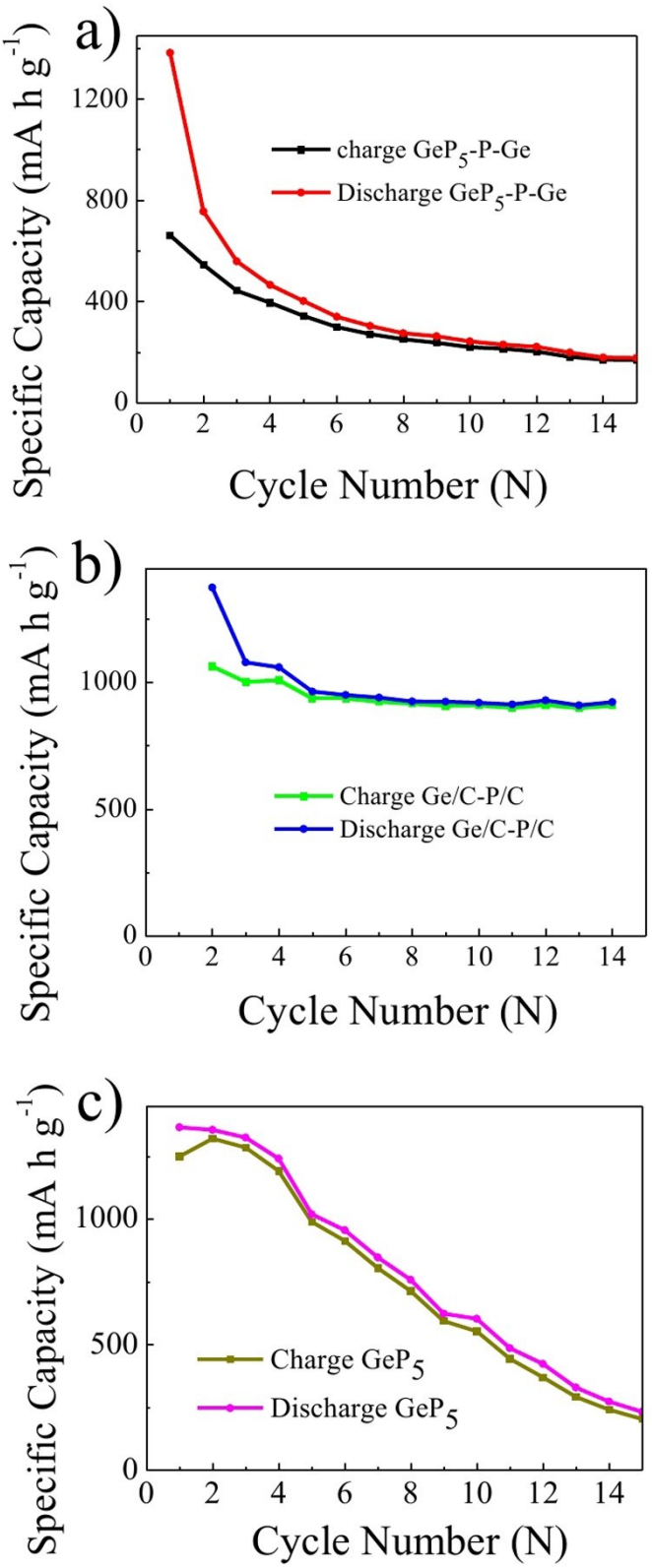

Figure S11. The electrochemical performances of a) the as-synthesized the medium GeP_5-P-Ge composite; b) the Ge/C-P/C composite; c) pure GeP_5.

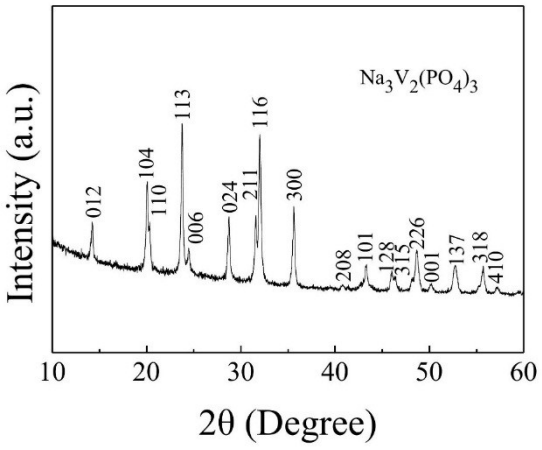

Figure S12. The XRD pattern of $Na_3V_2(PO_4)_3$/C.

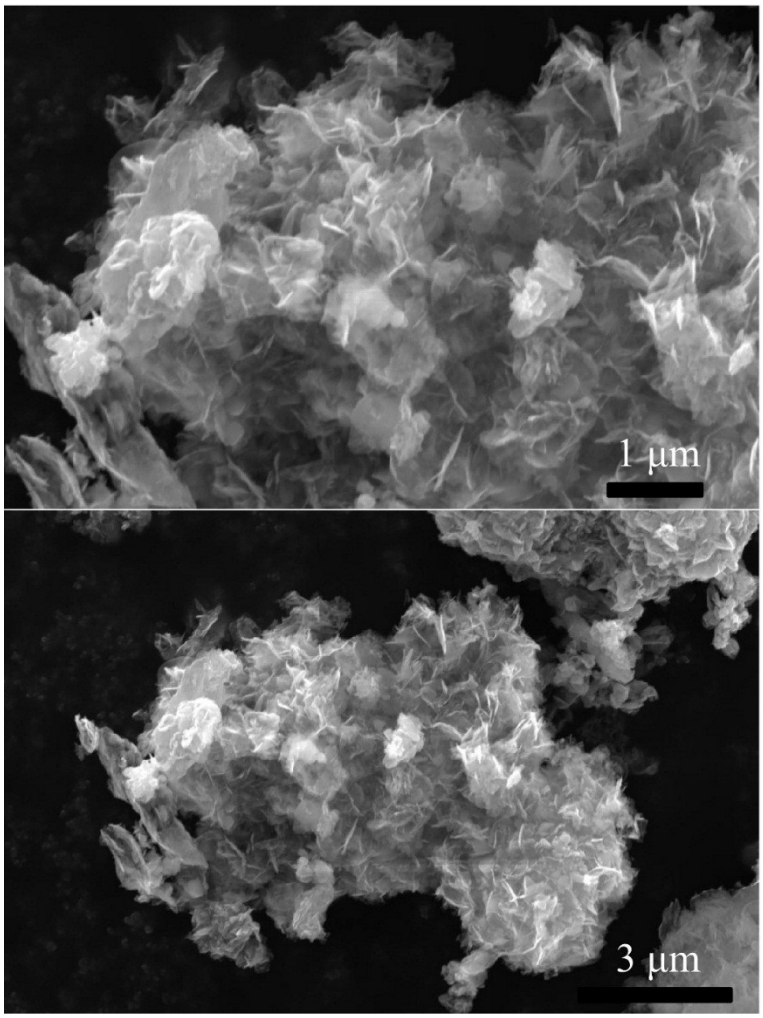

Figure S13. The FSEM images of $Na_3V_2(PO_4)_3$/C.

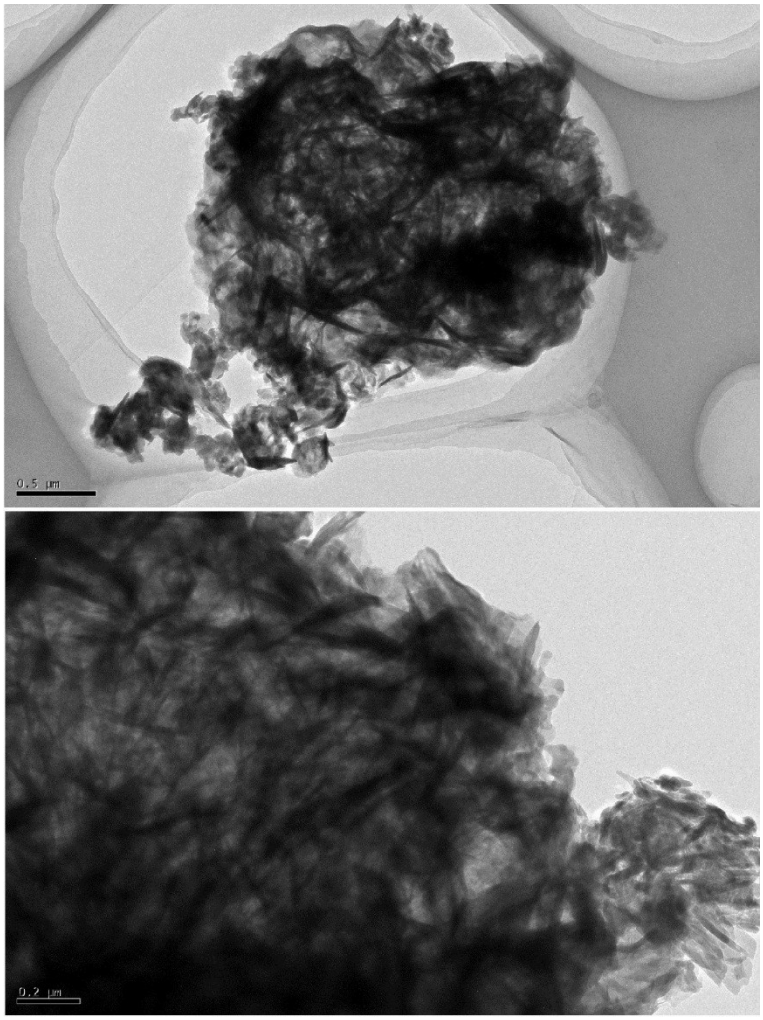

Figure S14. The TEM images of $Na_3V_2(PO_4)_3$/C.

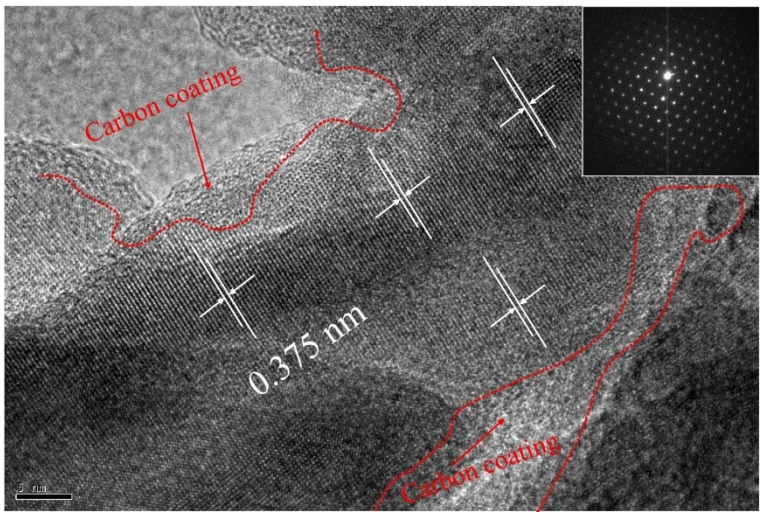

Figure S15. The TEM images of $Na_3V_2(PO_4)_3$/C.